TMG130N06LNF

N -Channel Enhancement Mosfet

General Description

- Low R $_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

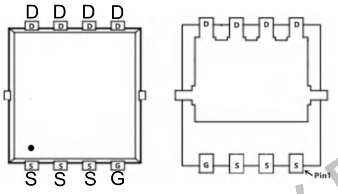
V_{DS} = 60V I_D = 130A

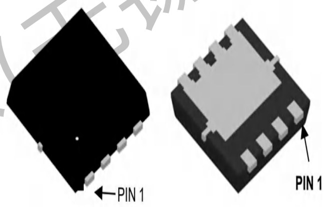
$R_{DS(ON)}$=2.4mΩ(typ.)@V_{GS}=10V

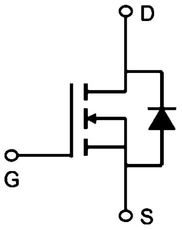
100% UIS Tested

100% R_g Tested

NF:DFN5x6-8L







Marking: G130N06

Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25˚C	Continuous Drain Current, V_{GS} @ 10V	130	A
I_D@T_C=100˚C	Continuous Drain Current, V_{GS} @ 10V	101	A
I_{DM}	Pulsed Drain Current	641	A
EAS	Single Pulse Avalanche Energy	189	mJ
P_D	Total Power Dissipation	113	W
T_{STG}	Storage Temperature Range	-55 to 175	˚C
T_J	Operating Junction Temperature Range	-55 to 175	˚C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	---	62	˚C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	3.6	˚C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Static Characteristics

Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	60	--	--	V
I_{DSS}	Drain to Source Leakage Current	V_{DS} = 60V, V_{GS}= 0V	--	--	1	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS} =+20V	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS} =-20V	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D = 250μA	1	1.5	2	V
$R_{DS(ON)}$	Drain-to-Source On-Resistance	V_{GS}=10V, I_D=20A	--	2.4	3.5	mΩ
		V_{GS}=4.5V, I_D=10A	--	3.6	4.2	

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 30V f = 1.0MHz	--	4610	6915	pF
C_{oss}	Output Capacitance		--	2188	3282	
C_{rss}	Reverse Transfer Capacitance		--	66	132	
R_g	Gate resistance		--	0.93	18.8	Ω

Resistive Switching Characteristics

Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	I_D =40A V_{DS} = 30V V_{GS} = 10V R_G= 2.7Ω	--	14.13	--	ns
tr	Rise Time		--	63.73	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	46.8	--	
t_f	Fall Time		--	105.07	--	
Q_g	Total Gate Charge	V_{GS} =10V V_{DS} = 30V I_D =40A	--	74.37	111.56	nC
Q_{gs}	Gate Source Charge		--	17.26	--	
Q_{gd}	Gate Drain Charge		--	9.44	18.88	

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	T_C =25 °C	--	--	130	A
V_{SD}	Diode Forward Voltage	I_S=40A, V_{GS}=0V	--	0.83	1.2	V
t_{rr}	Reverse Recovery time	I_S=40A, dI/dt=300A/μs	--	52.78	105.56	ns
Q_{rr}	Reverse Recovery Charge		--	56.31	112.62	nC

Typical Characteristics

Fig 1: Output Characteristics

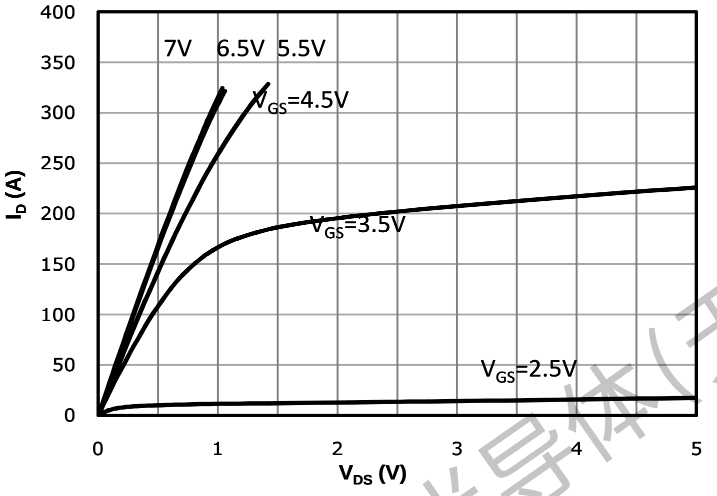


Fig 2: Transfer Characteristics

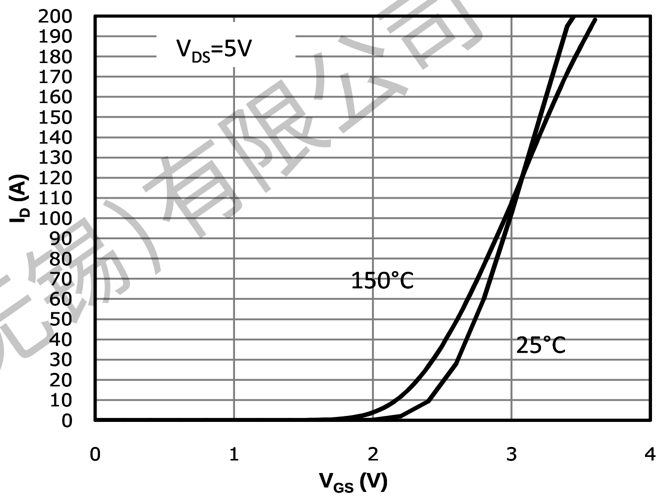


Fig 3: Rds(on) vs Drain Current and Gate Voltage

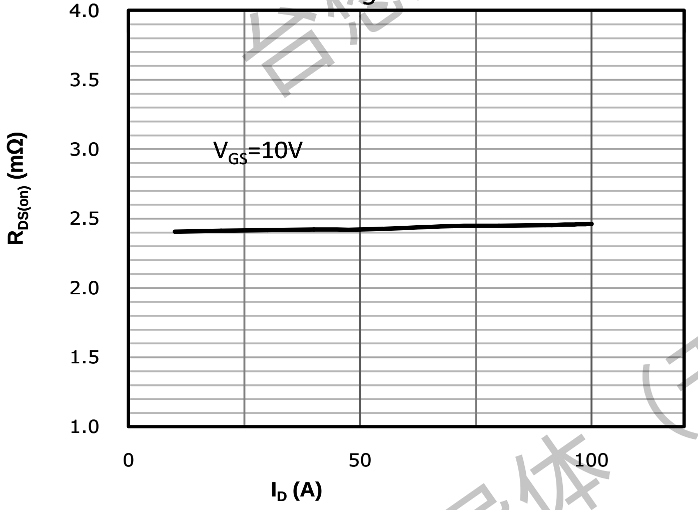


Fig 4: Rds(on) vs Gate Voltage

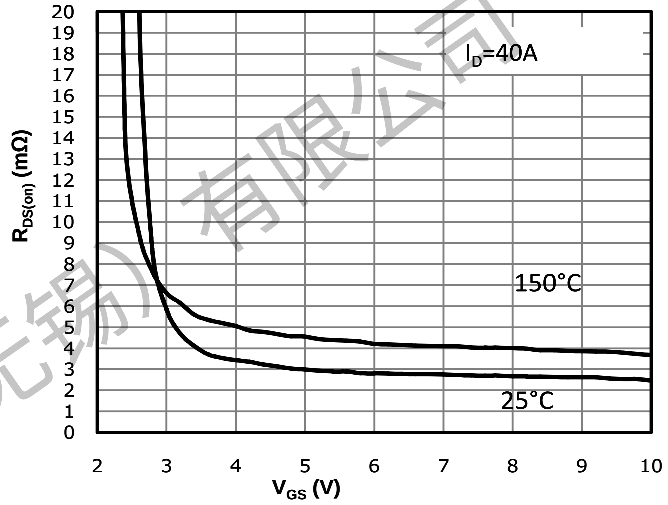


Fig 5: Rds(on) vs. Temperature

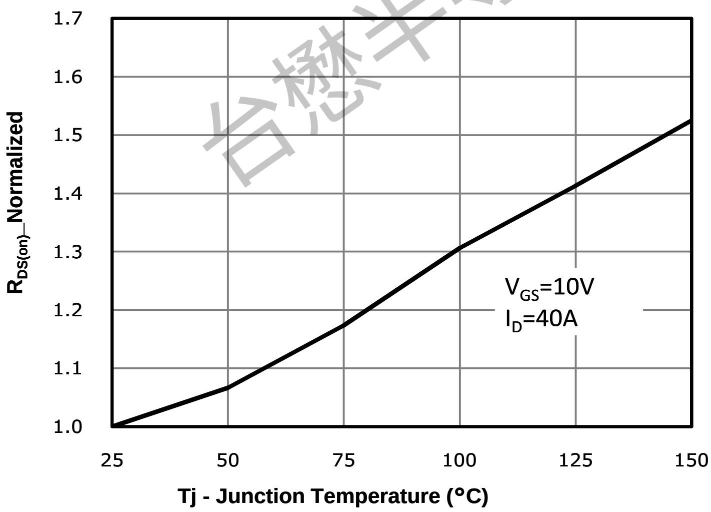


Fig 6: Capacitance Characteristics

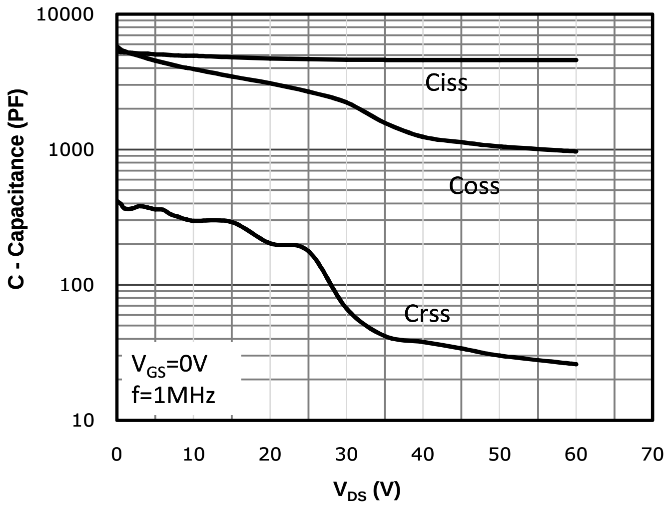


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Fig 7: Gate ChargeCharacteristics

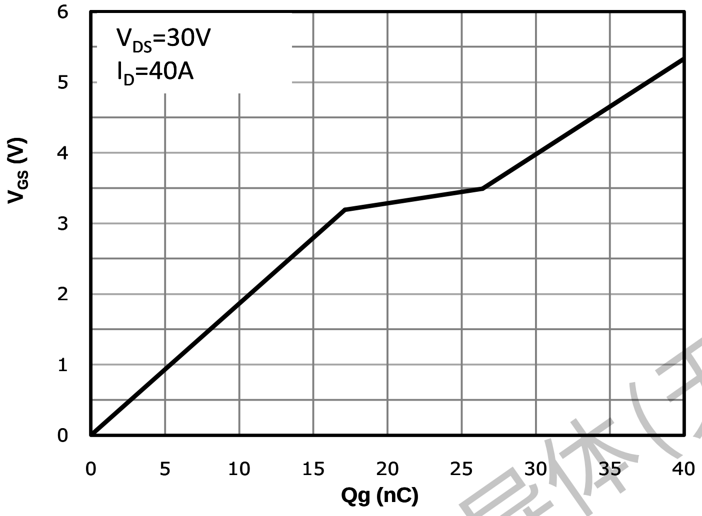


Fig 8: Body-diode Forward Characteristics

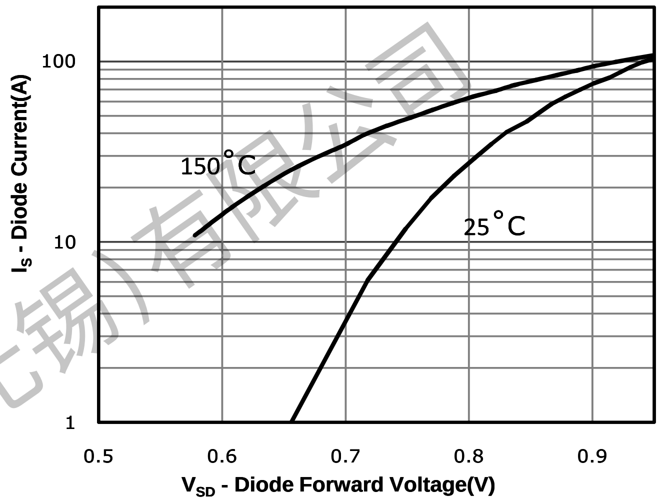


Fig 9: Power Dissipation

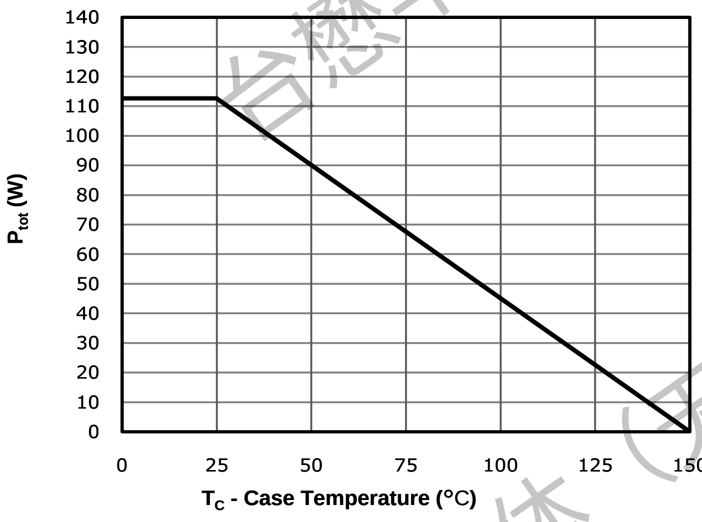


Fig 10: Drain Current Derating

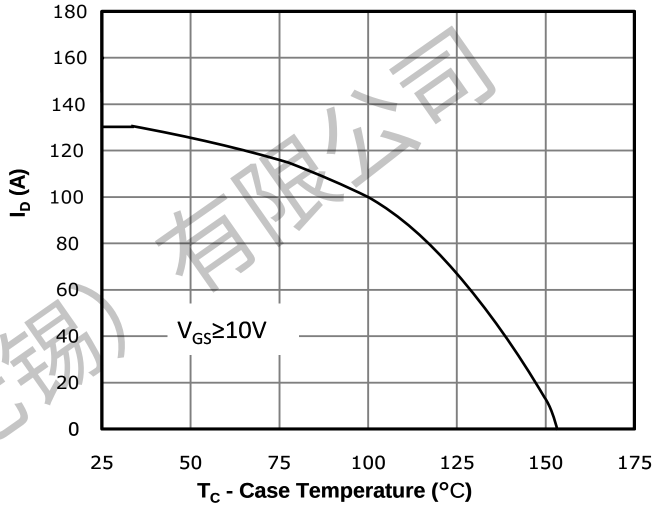


Fig 11: Safe Operating Area

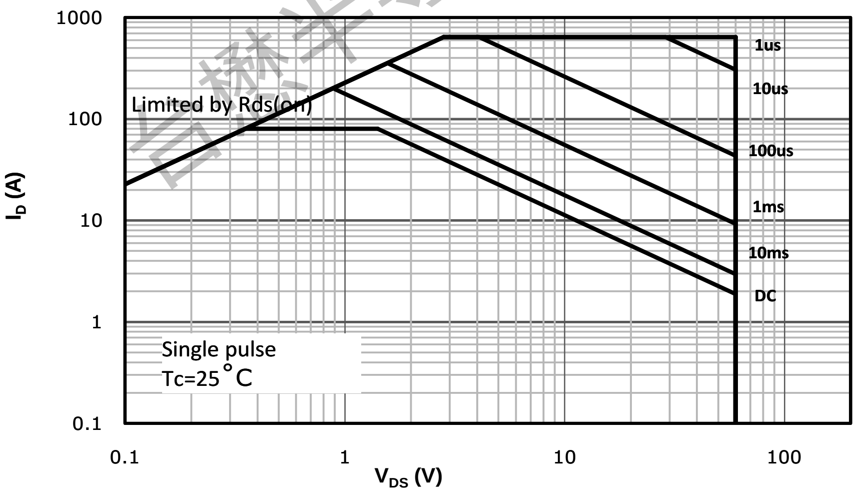
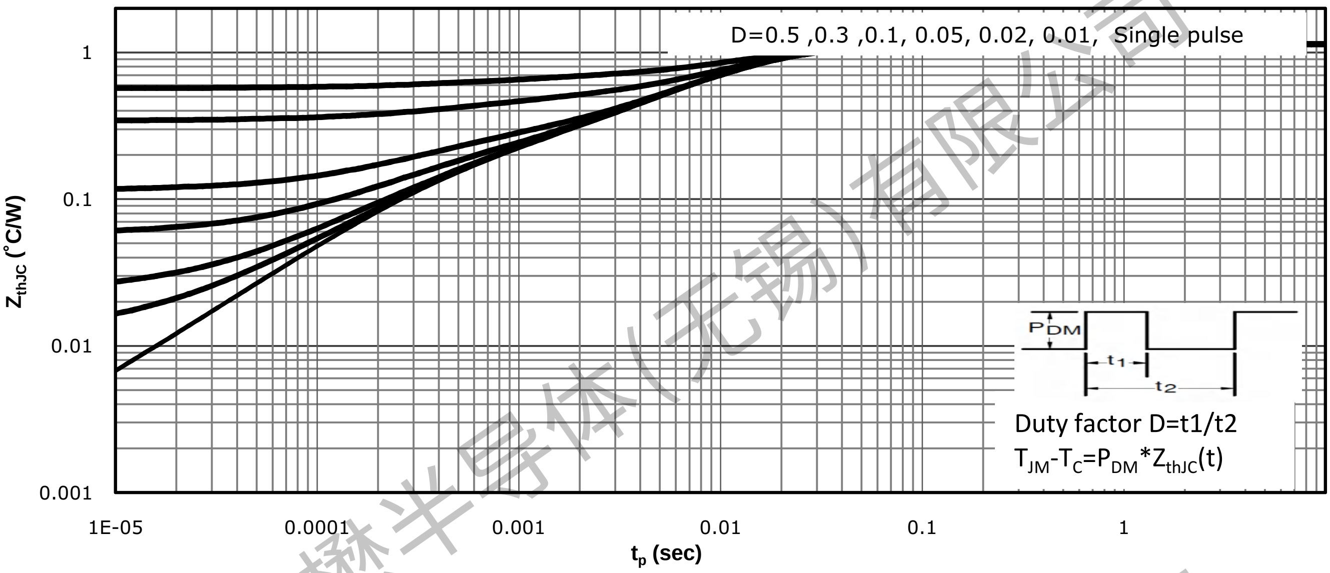
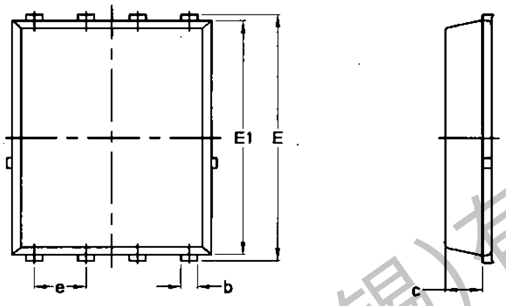
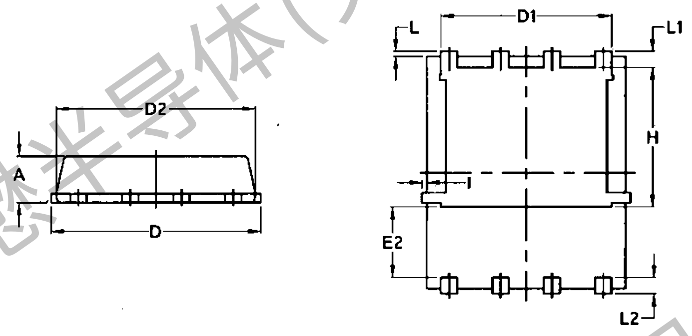


Fig 12: Max. Transient Thermal Impedance



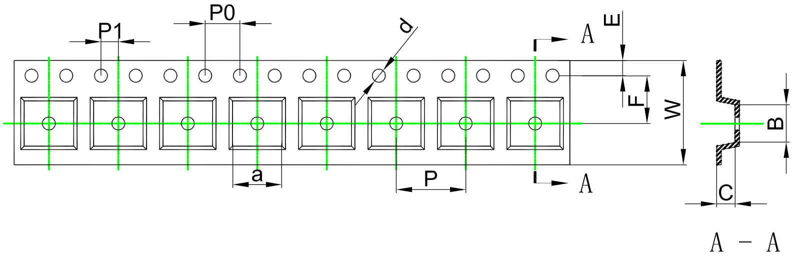
Package Mechanical Data:DFN5x6-8L





Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

PDFN5×6-8L Embossed Carrier Tape



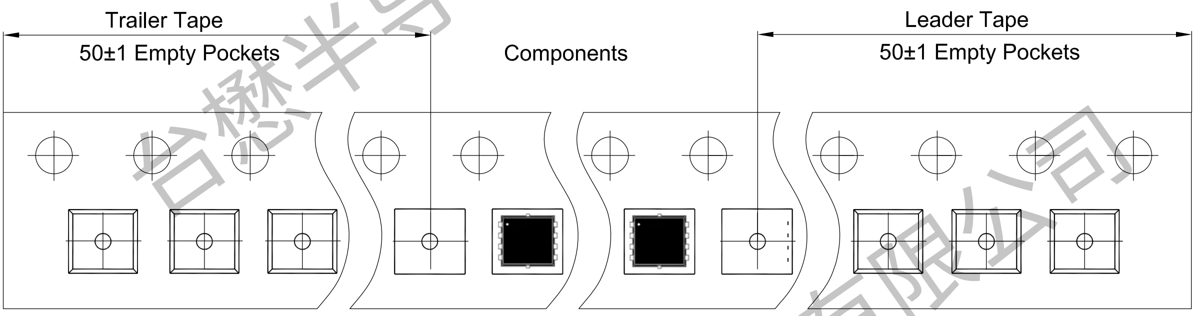
Packaging Description:

SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

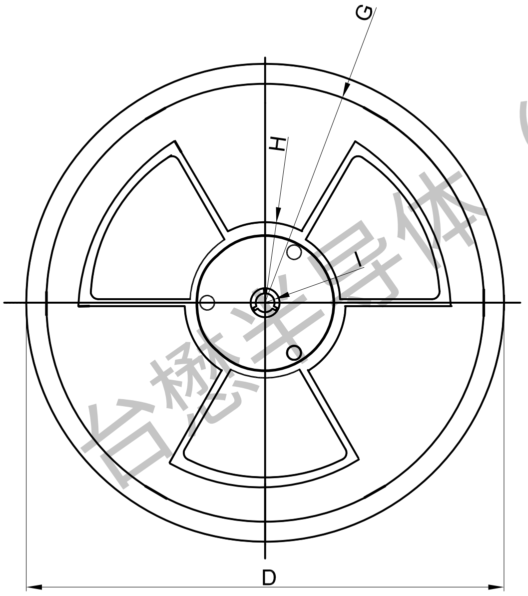
ALL DIM IN mm

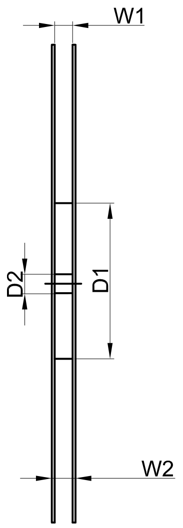
Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
PDFN5×6-8L	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFN5×6-8L Tape Leader and Trailer



PDFN5×6-8L Reel





Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13"Dia	Ø330.00	100.00	13.00	R135.00	R55.00	R6.50	12.00	14.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
5,000 pcs	13 inch	10,000 pcs	370×355×52	50,000 pcs	400×360×368	

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Revision history:

Date	Rev	Description	Page
2023.08.14	23.08	Original	